

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.116
Serial Number: 10/788,899
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Title: METHOD OF FORMING HIGH ASPECT RATIO STRUCTURES

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Dkt: 303.866US1

IN THE CLAIMS

DO NOT ENTER: /AA/

Please amend the claims as follows:

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1. (Previously Presented) A process comprising:
 - forming a first dielectric layer on a substrate;
 - forming a second dielectric layer on the first dielectric layer;
 - forming a first recess having a first lateral dimension at a bottom portion of the first dielectric layer in contact with the substrate, and having a second lateral dimension at a top portion of the second dielectric layer;
 - forming a conductive structure in the first recess having vertical sidewalls with the first lateral dimension having a value approximately equal to a value of the second lateral dimension;
 - first wet etching to expose a first portion of the conductive structure by removing at least a portion of the second dielectric layer;
 - first rinsing the conductive structure; and
 - second non-wet etching to expose a second portion of the conductive structure by removing at least a remaining portion of the first dielectric layer and exposing at least a portion of the substrate.
2. (Currently Amended) The process of claim 1, wherein ~~first wet etching includes first etching the second dielectric film includes~~ a polysilicon ~~sacrificial second film that is disposed over the substrate.~~
3. (Currently Amended) The process of claim 1, ~~and~~ wherein first wet etching has ~~is at~~ a rate that is faster than second non-wet etching.
4. (Currently Amended) The process of claim 1. ~~A process comprising:~~
 - ~~forming a first dielectric layer on a substrate;~~
 - ~~forming a second dielectric layer on the first dielectric layer;~~
 - ~~forming a first recess in the first and second dielectric layer to expose a portion of the substrate;~~